DATASHEET

The 9FGL06 devices are 3.3V members of IDT's 3.3V Full-Featured PCIe family. The devices have 6 output enables for clock management and support 2 different spread spectrum levels in addition to spread off. The 9FGL06 supports PCIe Gen1-4 Common Clocked architectures (CC) and PCIe Separate Reference no-Spread (SRnS) and Separate Reference Independent Spread (SRIS) clocking architectures. The 9FGL06P1 can be programmed with a user-defined power up default SMBus configuration.

Recommended Application

PCIe Gen1-4 clock generation for Riser Cards, Storage, Networking, JBOD, Communications, Access Points

Output Features

Description

- 6 100 MHz Low-Power HCSL (LP-HCSL) DIF pairs
 - 9FGL0641 default ZOUT = 100Ω
 - 9FGL0651 default ZOUT = 85Ω
 - 9FGL06P1 factory programmable defaults
- 1 3.3V LVCMOS REF output w/Wake-On-LAN (WOL) support
- Easy AC-coupling to other logic families, see IDT application note <u>AN-891</u>

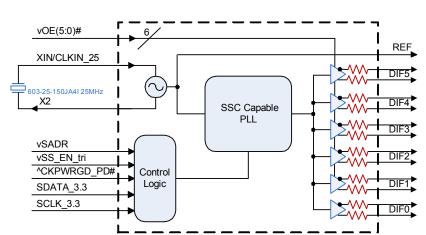
Key Specifications

- PCIe Gen1-2-3-4 CC-compliant
- PCIe Gen2-3 SRIS-compliant
- DIF cycle-to-cycle jitter <50ps
- DIF output-to-output skew <50ps
- DIF 12k-20M phase jitter is <2ps rms when SSC is off
- REF phase jitter is <300fs rms, SSC off, and <1.5ps rms, SSC is On
- ±100ppm frequency accuracy on all clocks

Block Diagram

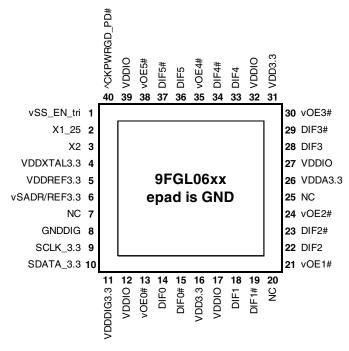


- Direct connection to 100Ω (xx41) or 85Ω (xx51) transmission lines; saves 24 resistors compared to standard PCIe devices
- 172mW typical power consumption (@3.3V); eliminates thermal concerns
- SMBus-selectable features allows optimization to customer requirements:
 - · control input polarity
 - · control input pull up/downs
 - · slew rate for each output
 - differential output amplitude
 - 33, 85 or 100Ω output impedance for each output
 - spread spectrum amount
- 41 and 51 devices contain default configuration; SMBus interface not required for device operation
- P1 device allows factory programming of customer-defined SMBus power up default; allows exact optimization to customer requirements
- 8MHz 40MHz input frequency with 9FGL08P1 device (25MHz default); flexibility
- OE# pins; support DIF power management
- Pin/SMBus selectable 0%, -0.25% or -0.5% spread on DIF outputs; minimize EMI and phase jitter for each application
- DIF outputs blocked until PLL is locked; clean system start-up
- Two selectable SMBus addresses; multiple devices can easily share an SMBus segment
- Space saving 40-pin 5x5mm VFQFPN; minimal board space



Note: Resistors default to internal on 41/51 devices. P1 devices have programmable default impedances on an output-by-output basis.

Pin Configuration



40-pin VFQFPN, 5x5 mm, 0.4mm pitch

- v prefix indicates internal 120KOhm pull down resistor
- ^ prefix indicates internal 120KOhm pull up resistor

SMBus Address Selection Table

	SADR	Address	+ Read/Write Bit
State of SADR on first application	0	1101000	Х
of CKPWRGD_PD#	1	1101010	Х

Power Management Table³

CKPWRGD_PD#	SMBus	OEx# Pin	DIF	REF		
	OE bit		True O/P	Comp. O/P		
0	Х	Х	Low ¹	Low ¹	Hi-Z ²	
1	1	0	Running	Running	Running	
1	1	1	Disabled ¹	Disabled ¹	Running	
1	0	Х	Disabled ¹	Disabled ¹	Disabled ⁴	

1. The output state is set by B11[1:0] (Low/Low default)

2. REF is Hi-Z until the 1st assertion of CKPWRGD_PD# high. After this, when CKPWRG_PD# is low, REF is disabled unless Byte3[5]=1, in which case REF is running.

3. Input polarities defined at default values for 9FGL0641/0651.

4. See SMBus description for Byte 3, bit 4

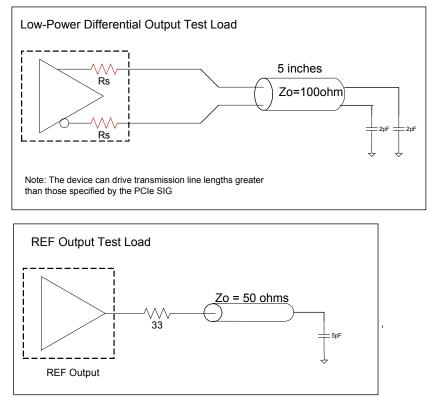
Power Connections

Pin Number			Description
VDD	VDDIO	GND	Description
4		41	XTAL OSC
5		41	REF Power
11		8	Digital (dirty) Power
	12,17,27,32,39	41	DIF outputs
26		41	PLL Analog

Pin Descriptions

PIN #	PIN NAME	PIN TYPE	DESCRIPTION
1	vSS_EN_tri	LATCHED	Latched select input to select spread spectrum amount at initial power up :
I	V35_EN_III	IN	1 = -0.5% spread, M = -0.25%, 0 = Spread Off
2	X1_25	IN	Crystal input, Nominally 25.00MHz.
3	X2	OUT	Crystal output.
4	VDDXTAL3.3	PWR	Power supply for XTAL, nominal 3.3V
5	VDDREF3.3	PWR	VDD for REF output. nominal 3.3V.
6	vSADR/REF3.3	LATCHED I/O	Latch to select SMBus Address/3.3V LVCMOS copy of X1/REFIN pin
7	NC	N/A	No Connection.
8	GNDDIG	GND	Ground pin for digital circuitry
9	SCLK_3.3	IN	Clock pin of SMBus circuitry, 3.3V tolerant.
10	SDATA_3.3	I/O	Data pin for SMBus circuitry, 3.3V tolerant.
11	VDDDIG3.3	PWR	3.3V digital power (dirty power)
12	VDDIO	PWR	Power supply for differential outputs
13	vOE0#	IN	Active low input for enabling DIF pair 0. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
14	DIF0	OUT	Differential true clock output
	DIF0#	OUT	Differential Complementary clock output
	VDD3.3	PWR	Power supply, nominal 3.3V
17	VDDIO	PWR	Power supply for differential outputs
-	DIF1	OUT	Differential true clock output
	DIF1#	OUT	Differential Complementary clock output
	NC	N/A	No Connection.
21	vOE1#	IN	Active low input for enabling DIF pair 1. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
22	DIF2	OUT	Differential true clock output
	DIF2#	OUT	Differential Complementary clock output
	vOE2#	IN	Active low input for enabling DIF pair 2. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
25	NC	N/A	No Connection.
26	VDDA3.3	PWR	3.3V power for the PLL core.
20	VDDIO	PWR	Power supply for differential outputs
28	DIF3	OUT	Differential true clock output
29	DIF3#		Differential Complementary clock output
	vOE3#	IN	Active low input for enabling DIF pair 3. This pin has an internal pull-down.
21	VDD3.3	PWR	1 =disable outputs, 0 = enable outputs Power supply, nominal 3.3V
31 32	VDD3.3	PWR	
			Power supply for differential outputs
	DIF4		Differential true clock output
34	DIF4#	OUT	Differential Complementary clock output Active low input for enabling DIF pair 4. This pin has an internal pull-down.
35	vOE4#	IN	1 =disable outputs, 0 = enable outputs
36	DIF5	OUT	Differential true clock output
37	DIF5#	OUT	Differential Complementary clock output
38	vOE5#	IN	Active low input for enabling DIF pair 5. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
39	VDDIO	PWR	Power supply for differential outputs
40	^CKPWRGD_PD#	IN	Input notifies device to sample latched inputs and start up on first high assertion. Low enters Power Down Mode, subsequent high assertions exit Power Down Mode. This pin has internal
			pull-up resistor.
41	ePAD	GND	Connect paddle to ground.

Test Loads



Terminations

Device	Ζο (Ω)	Rs (Ω)
9FGL0641	100	None needed
9FGL0651	100	7.5
9FGL06P1	100	Prog.
9FGL0641	85	N/A
9FGL0651	85	None needed
9FGL06P1	85	Prog.

Alternate Terminations

The 9FGL family can easily drive LVPECL, LVDS, and CML logic. See <u>"AN-891 Driving LVPECL, LVDS, and CML Logic with</u> <u>IDT's "Universal" Low-Power HCSL Outputs</u>" for details.

Absolute Maximum Ratings

Stresses above the ratings listed below can cause permanent damage to the 9FGL06. These ratings, which are standard values for IDT commercially rated parts, are stress ratings only. Functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods can affect product reliability. Electrical parameters are guaranteed only over the recommended operating temperature range.

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
3.3V Supply Voltage	VDDxx	Applies to VDD, VDDA and VDDIO, if present.	-0.5		3.9	V	1,2
Input Voltage	V _{IN}		-0.5		V _{DD} + 0.5V	V	1, 3
Input High Voltage, SMBus	VIHSMB	SMBus clock and data pins			3.9	V	1
Storage Temperature	Ts		-65		150	°C	1
Junction Temperature	Tj				125	°C	1
Input ESD protection	ESD prot	Human Body Model	2500			V	1

¹Guaranteed by design and characterization, not 100% tested in production.

² Operation under these conditions is neither implied nor guaranteed.

³ Not to exceed 4.5V.

Electrical Characteristics-SMBus Parameters

TA = T_{AMB;} Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
SMBus Input Low Voltage	VILSMB	$V_{DDSMB} = 3.3V$			0.8	V	
SMBus Input High Voltage	VIHSMB	$V_{DDSMB} = 3.3V$	2.1		3.6	V	
SMBus Output Low Voltage	V _{OLSMB}	@ I _{PULLUP}			0.4	V	
SMBus Sink Current	I _{PULLUP}	@ V _{OL}	4			mA	
Nominal Bus Voltage	V _{DDSMB}		2.7		3.6	V	
SCLK/SDATA Rise Time	t _{RSMB}	(Max VIL - 0.15) to (Min VIH + 0.15)			1000	ns	1
SCLK/SDATA Fall Time	t _{FSMB}	(Min VIH + 0.15) to (Max VIL - 0.15)			300	ns	1
SMBus Operating Frequency	f _{SMB}	SMBus operating frequency			500	kHz	2

¹ Guaranteed by design and characterization, not 100% tested in production.

^{2.} The device must be powered up for the SMBus to function.

Electrical Characteristics–Input/Supply/Common Parameters–Normal Operating Conditions

TAMB; Ouppiy Voltagoo	per normai e	peration conditions, dec rest codes for codding o	onantionio				
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	МАХ	UNITS	NOTES
Supply Voltage	VDDxxx	Supply voltage for core, analog and single-ended LVCMOS outputs.	3.135	3.3	3.465	V	
IO Supply Voltage	VDDIO	Supply voltage for differential Low Power outputs.	0.9975	1.05-3.3	3.465	V	
Ambient Operating Temperature	T _{AMB}	Industrial range	-40	25	85	°C	
Input High Voltage	V _{IH}	Single-ended inputs, except SMBus	0.75 V _{DDx}		V _{DDx} + 0.3	V	
Input Low Voltage	VIL		-0.3		0.25 V _{DDx}	V	
Input High Voltage	V _{IHtri}		0.75 V _{DDx}		V _{DD} + 0.3	V	
Input Mid Voltage	V _{IMtri}	Single-ended tri-level inputs ('_tri' suffix)	0.4 V _{DDx}	0.5 V _{DDx}	0.6 V _{DDx}	V	
Input Low Voltage	V _{ILtri}		-0.3		0.25 V _{DDx}	V	
	I _{IN}	Single-ended inputs, $V_{IN} = GND$, $V_{IN} = VDD$	-5		5	uA	
Input Current	I _{INP}	Single-ended inputs $V_{IN} = 0 \text{ V}$; Inputs with internal pull-up resistors $V_{IN} = \text{VDD}$; Inputs with internal pull-down resistors	-50		50	uA	
Input Frequency	F _{in}	XTAL, or X1 input	8	25	40	MHz	4
Pin Inductance	L _{pin}				7	nH	1
Capacitance	C _{IN}	Logic Inputs, except DIF_IN	1.5		5	pF	1
Capacitance	C _{OUT}	Output pin capacitance			6	pF	1
Clk Stabilization	T _{STAB}	From V_{DD} Power-Up and after input clock stabilization or de-assertion of PD# to 1st clock		0.3	1.8	ms	1,2
SS Modulation Frequency	f _{MOD}	(Triangular Modulation)	30	31.6	33	kHz	1
OE# Latency	t _{LATOE#}	DIF start after OE# assertion DIF stop after OE# deassertion	1	2	3	clocks	1,3
Tdrive_PD#	t _{DRVPD}	DIF output enable after PD# de-assertion		28	300	us	1,3
Tfall	t _F	Fall time of single-ended control inputs			5	ns	1,2
Trise	t _R	Rise time of single-ended control inputs			5	ns	1,2

TA = T_{AMB}; Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

¹ Guaranteed by design and characterization, not 100% tested in production.

² Control input must be monotonic from 20% to 80% of input swing.

³ Time from deassertion until outputs are >200 mV

⁴ The 9FGLxxP1 devices can be programmed for various input frequencies from 8 to 40MHz. The 9FGLxx41/51 devices use 25MHz.

Electrical Characteristics–DIF Low-Power HCSL Outputs

TA = T_{AMB;} Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

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PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Slew rate	Trf	Scope averaging on, fast setting	2	2.7	4	V/ns	2,3
Slew fale	111	Scope averaging, slow setting	1	1.9	3	V/ns	2,3
Crossing Voltage (abs)	Vcross_abs	Scope averaging off	250	409	550	mV	1,4,5
Crossing Voltage (var)	∆-Vcross	Scope averaging off		14	140	mV	1,4,9
Avg. Clock Period Accuracy	T _{PERIOD_AVG}		-100	0.0	+2600	ppm	2,10,13
Absolute Period	T _{PERIOD_ABS}	Includes jitter and Spread Spectrum Modulation	9.94906	10.0	10.1011	ns	2,6
Jitter, Cycle to cycle	t _{jcyc-cyc}			16	50	ps	2
Voltage High	V _{HIGH}	Statistical measurement on single-ended signal using oscilloscope math function. (Scope	660	761	850	mV	1
Voltage Low	V_{LOW}	averaging on)	-150	-7	150	IIIV	1
Absolute Max Voltage	Vmax	Measurement on single ended signal using		819	1150	mV	1,7,15
Absolute Min Voltage	Vmin	absolute value. (Scope averaging off)	-300	-46		mv	1,8,15
Duty Cycle	t _{DC}		45	49	55	%	2
Slew rate matching	∆Trf			6	20	%	1,14
Skew, Output to Output	t _{sk3}	Averaging on, $V_T = 50\%$		35	50	ps	2

¹ Measured from single-ended waveform.

² Measured from differential waveform.

³ Measured from -150 mV to +150 mV on the differential waveform (derived from REFCLK+ minus REFCLK-). The signal must be monotonic through the measurement region for rise and fall time. The 300 mV measurement window is centered on the differential zero crossing.

⁴ Measured at crossing point where the instantaneous voltage value of the rising edge of REFCLK+ equals the falling edge of REFCLK-.

⁵ Refers to the total variation from the lowest crossing point to the highest, regardless of which edge is crossing. Refers to all crossing points for this measurement.

⁶ Defines as the absolute minimum or maximum instantaneous period. This includes cycle to cycle jitter, relative PPM tolerance, and spread spectrum modulation.

⁷ Defined as the maximum instantaneous voltage including overshoot.

⁸ Defined as the minimum instantaneous voltage including undershoot.

⁹ Defined as the total variation of all crossing voltages of Rising REFCLK+ and Falling REFCLK-. This is the maximum allowed variance in V_{CROSS} for any particular system.

¹⁰ Refer to Section 4.3.7.1.1 of the PCI Express Base Specification, Revision 3.0 for information regarding PPM considerations.

¹¹ System board compliance measurements must use the test load. REFCLK+ and REFCLK- are to be measured at the load capacitors CL. Single ended probes must be used for measurements requiring single ended measurements. Either single ended probes with math or differential probe can be used for differential measurements. Test load CL = 2 pF.

¹² T_{STABLE} is the time the differential clock must maintain a minimum ±150 mV differential voltage after rising/falling edges before it is allowed to droop back into the VRB ±100 mV differential range.

¹³ PPM refers to parts per million and is a DC absolute period accuracy specification. 1 PPM is 1/1,000,000th of 100.000000 MHz exactly or 100 Hz. For 300 PPM, then we have an error budget of 100 Hz/PPM * 300 PPM = 30 kHz. The period is to be measured with a frequency counter with measurement window set to 100 ms or greater. The \pm 300 PPM applies to systems that do not employ Spread Spectrum Clocking, or that use common clock source. For systems employing Spread Spectrum Clocking, there is an additional 2,500 PPM nominal shift in maximum period resulting from the 0.5% down spread resulting in a maximum average period specification of +2,800 PPM.

¹⁴ Matching applies to rising edge rate for REFCLK+ and falling edge rate for REFCLK-. It is measured using a ±75 mV window centered on the median cross point where REFCLK+ rising meets REFCLK- falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations. The Rise Edge Rate of REFCLK+ should be compared to the Fall Edge Rate of REFCLK-; the maximum allowed difference should not exceed 20% of the slowest edge rate.

¹⁵ At default SMBus amplitude settings.

Electrical Characteristics–Filtered Phase Jitter Parameters - PCIe Common Clocked (CC) Architectures

T_{AMB} = over the specified operating range. Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	INDUSTRY LIMIT	UNITS	Notes
	t _{jphPCleG1-CC}	PCIe Gen 1		19	28	86	ps (p-p)	1,2,3
	t _{jphPCleG2-CC}	PCIe Gen 2 Lo Band 10kHz < f < 1.5MHz (PLL BW of 5-16MHz or 8-5MHz, CDR = 5MHz)		0.4	0.6	3	ps (rms)	1,2
Phase Jitter		PCIe Gen 2 High Band 1.5MHz < f < Nyquist (50MHz) (PLL BW of 5-16MHz or 8-5MHz, CDR = 5MHz)		1.2	1.9	3.1	ps (rms)	1,2
	t _{jphPCleG3-CC}	PCIe Gen 3 (PLL BW of 2-4MHz or 2-5MHz, CDR = 10MHz)		0.3	0.45	1	ps (rms)	1,2
	t _{jphPCleG4-CC}	PCIe Gen 4 (PLL BW of 2-4MHz or 2-5MHz, CDR = 10MHz)		0.3	0.45	0.5	ps (rms)	1,2

¹ Applies to all outputs.

² Based on PCIe Base Specification Rev4.0 version 0.7draft. See http://www.pcisig.com for latest specifications.

³ Sample size of at least 100K cycles. This figures extrapolates to 108ps pk-pk @ 1M cycles for a BER of 1-12.

Electrical Characteristics–Filtered Phase Jitter Parameters - PCIe Separate Reference Independent Spread (SRIS) Architectures

T_{AMB} = over the specified operating range. Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	INDUSTRY LIMIT	UNITS	Notes
Phase Jitter, PLL Mode	t _{jphPCleG2-} SRIS	PCIe Gen 2 (PLL BW of 16MHz , CDR = 5MHz)		0.7	1.1	2	ps (rms)	1,2
	t _{jphPCleG3-} SRIS	PCIe Gen 3 (PLL BW of 2-4MHz or 2-5MHz, CDR = 10MHz)		0.5	0.65	0.7	ps (rms)	1,2

¹ Applies to all outputs.

² Based on PCIe Base Specification Rev3.1a. These filters are different than Common Clock filters. See http://www.pcisig.com for latest specifications. There is a proposal to reduce the PCIe Gen3 limit to 0.5ps.

³ As of PCIe Base Specification Rev4.0 draft 0.7, SRIS is not currently defined for Gen1 or Gen4.

Electrical Characteristics–DIF LP-HCSL Output Unfiltered Phase Jitter Parameters

TA = T_{AMB;} Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	INDUSTRY LIMIT	UNITS
Phase Jitter, 12k-20M	t _{jph12k20M}	100MHz outputs with REF output enabled SSC Off		1.5	2	N/A	ps (rms)

Electrical Characteristics–Current Consumption

TA = T_{AMB;} Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

/							1
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
	I _{DDAOP}	VDDA, All outputs active @100MHz	100MHz 13 18 mA O, All outputs 16 22 mA 100MHz 24 28 mA 100MHz 24 28 mA 100MHz 0.9 1.5 mA vDDIO, running 6.2 9.0 mA utput running 0.04 0.1 mA f 0.9 1.5 mA , all outputs off 1.8 2.5 mA				
Operating Supply Current	I _{DDOP}	All VDD, except VDDA and VDDIO, All outputs active @100MHz		16	22	mA	
	I _{DDIOOP}	VDDIO, All outputs active @100MHz	@ 100MHz 13 18 mA DIO, All outputs 16 22 mA @ 100MHz 24 28 mA @ 100MHz 0.9 1.5 mA output running 0.9 1.5 mA output running 6.2 9.0 mA output running 0.04 0.1 mA off 0.9 1.5 mA IO, all outputs off 1.8 2.5 mA				
Wake-on-LAN Current	I _{DDAPD}	VDDA, DIF outputs off, REF output running		0.9	1.5	mA	1
(Power down state and Byte 3, bit 5 = '1')	I _{DDPD}	All VDD, except VDDA and VDDIO, DIF outputs off, REF output running		6.2	9.0	mA	1
byte 3, bit 5 = 1)	I _{DDIOPD}	VDDIO, DIF outputs off, REF output running		0.04	22 mA 28 mA 1.5 mA 9.0 mA 0.1 mA 1.5 mA 2.5 mA	1	
Powerdown Current	Powerdown Current IDDAPD VDDA, all outputs off			0.9	1.5	mA	
(Power down state and	I _{DDPD}	All VDD, except VDDA and VDDIO, all outputs off		1.8	2.5	mA	
Byte 3, bit 5 = '0')	I _{DDIOPD}	VDDIO, all outputs off		0.04	0.1	mA	

¹ This is the current required to have the REF output running in Wake-on-LAN mode (Byte 3, bit 5 = 1)

Electrical Characteristics- REF

TA = T_{AMB;} Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

		<u> </u>					
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	Notes
Long Accuracy	ppm	see Tperiod min-max values		0		ppm	1,2
Clock period	T _{period}	REF output		40		ns	2
High output Voltage	V _{HIGH}	loh = -2mA	0.8xV _{DDREF}			V	
Low output Voltage	V _{LOW}	Iol = 2mA			$0.2 \mathrm{xV}_{\mathrm{DDREF}}$	V	
Rise/Fall Slew Rate	t _{rf1}	Byte 3 = 1F, V _{OH} = 0.8*VDD, V _{OL} = 0.2*VDD	0.5	0.9	1.5	V/ns	1
Rise/Fall Slew Rate	t _{rf1}	Byte 3 = 5F, VOH = 0.8*VDD, VOL = 0.2*VDD	1.0	1.5	2.5	V/ns	1,3
Rise/Fall Slew Rate	t _{rf1}	Byte 3 = 9F, VOH = 0.8*VDD, VOL = 0.2*VDD	1.5	2.1	3.1	V/ns	1
Rise/Fall Slew Rate	t _{rf1}	Byte 3 = DF, VOH = 0.8*VDD, VOL = 0.2*VDD	2.0	2.7	3.8	V/ns	1
Duty Cycle	d _{t1X}	$V_T = VDD/2 V$	45	49.7	55	%	1,4
Duty Cycle Distortion	d _{tcd}	$V_T = VDD/2 V$	-1	0	0	%	1,5
Jitter, cycle to cycle	t _{jcyc-cyc}	$V_T = VDD/2 V$		35	125	ps	1,4
Noise floor	t _{jdBc1k}	1kHz offset		-145	-135	dBc	1,4
Noise floor	t _{jdBc10k}	10kHz offset to Nyquist		-150	-140	dBc	1,4
Jitter, phase	t _{jphREF}	12kHz to 5MHz, DIF SSC Off		0.132	0.3	ps (rms)	1,4

¹Guaranteed by design and characterization, not 100% tested in production.

² All Long Term Accuracy and Clock Period specifications are guaranteed assuming that REF is trimmed to 25.00 MHz

³ Default SMBus Value

⁴ When driven by a crystal.

⁵ When driven by an external oscillator via the X1 pin, X2 should be floating.

General SMBus Serial Interface Information

How to Write

- Controller (host) sends a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) sends the byte count = X
- IDT clock will **acknowledge**
- Controller (host) starts sending Byte N through Byte N+X-1
- IDT clock will acknowledge each byte one at a time
- Controller (host) sends a Stop bit

	Index Bl	ock V	/rite Operation
Controll	er (Host)		IDT (Slave/Receiver)
Т	starT bit		
Slave A	Address		
WR	WRite		
			ACK
Beginning	g Byte = N		
			ACK
Data Byte	Count = X		
			ACK
Beginnin	ng Byte N		
			ACK
0		×	
0		X Byte	0
0		Φ	0
			0
Byte N	+ X - 1		
			ACK
Р	stoP bit		

Note: SMBus Address is Latched on SADR pin. Unless otherwise indicated, default values are for the xx41 and xx51. P1 devices are fully factory programmable.

How to Read

- Controller (host) will send a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) will send a separate start bit
- Controller (host) sends the read address
- IDT clock will acknowledge
- IDT clock will send the data byte count = X
- IDT clock sends Byte N+X-1
- IDT clock sends Byte 0 through Byte X (if X_(H) was written to Byte 8)
- Controller (host) will need to acknowledge each byte
- Controller (host) will send a not acknowledge bit
- Controller (host) will send a stop bit

	Index Block F	lead O	peration
Cor	ntroller (Host)		IDT (Slave/Receiver)
Т	starT bit		
SI	ave Address		
WR	WRite		
		-	ACK
Begi	nning Byte = N	-	
		-	ACK
RT	Repeat starT	-	
SI	ave Address		
RD	ReaD		
			ACK
		-	Data Byte Count=X
	ACK		
		-	Beginning Byte N
	ACK	-	
		ę	0
	0	X Byte	0
	0	×	0
	0		
			Byte N + X - 1
N	Not acknowledge		
Р	stoP bit		

SMBus Table: Output Enable Register ¹

Byte 0	Name	Control Function	Туре	0	1	Default
Bit 7	DIF OE5	Output Enable	RW	See B11[1:0]	Pin controlled	1
Bit 6	DIF OE4	Output Enable	RW		Pin controlled	1
Bit 5	Reserved					
Bit 4	DIF OE3	Output Enable	RW		Pin controlled	1
Bit 3	DIF OE2	Output Enable	RW	See B11[1:0]	Pin controlled	1
Bit 2	DIF OE1	Output Enable	RW		Pin controlled	1
Bit 1	Reserved					
Bit 0	DIF OE0	Output Enable	RW	See B11[1:0]	Pin controlled	1

1. A low on these bits will overide the OE# pin and force the differential output to the state indicated by B11[1:0] (Low/Low default)

SMBus Table: SS Readback and Control Register

Byte 1	Name	Control Function	Туре	0	1	Default
Bit 7	SSENRB1	SS Enable Readback Bit1	R	00' for SS_EN_tri =	0, '01' for SS_EN_tri	Latch
Bit 6	SSENRB1	SS Enable Readback Bit0	R	= 'M', '11 for S	S_EN_tri = '1'	Latch
Bit 5	SSEN_SWCNTRL	Enable SW control of SS	RW	SS control locked	Values in B1[4:3] control SS amount.	0
Bit 4	SSENSW1	SS Enable Software Ctl Bit1	RW ¹	00' = SS Off, '0'	1' = -0.25% SS,	0
Bit 3	SSENSW0	SS Enable Software Ctl Bit0	RW ¹	'10' = Reserved	, '11'= -0.5% SS	0
Bit 2		Reserved				Х
Bit 1	AMPLITUDE 1	Controls Output Amplitude	RW	00 = 0.6V	01= 0.68V	1
Bit 0	AMPLITUDE 0		RW	10 = 0.75V	11 = 0.85V	0

1. B1[5] must be set to a 1 for these bits to have any effect on the part.

SMBus Table: DIF Slew Rate Control Register

Byte 2	Name	Control Function	Туре	0	1	Default
Bit 7	SLEWRATESEL DIF5	Adjust slew rate of DIF5	RW	Slow Setting	Fast Setting	1
Bit 6	SLEWRATESEL DIF4	Adjust slew rate of DIF4	RW	Slow Setting	Fast Setting	1
Bit 5	Reserved					
Bit 4	SLEWRATESEL DIF3	Adjust slew rate of DIF3	RW	Slow Setting	Fast Setting	1
Bit 3	SLEWRATESEL DIF2	Adjust slew rate of DIF2	RW	Slow Setting	Fast Setting	1
Bit 2	SLEWRATESEL DIF1	Adjust slew rate of DIF1	RW	Slow Setting	Fast Setting	1
Bit 1	Reserved					X
Bit 0	SLEWRATESEL DIF0	Adjust slew rate of DIF0	RW	Slow Setting	Fast Setting	1

Note: See "Low-Power HCSL Outputs" table for slew rates.

SMBus Table: Nominal Vhigh Amplitude Control/ REF Control Register

Byte 3	Name	Control Function	Туре	0	1	Default
Bit 7	REF	Slew Rate Control	RW	00 = Slowest	01 =Slow	0
Bit 6	NLI NLI	Siew Rate Control	RW	10 = Fast	11 = Fastest	1
Bit 5	REF Power Down Function	Wake-on-Lan Enable for REF	RW	REF disabled in Power Down	REF runs in Power Down	0
Bit 4	REF OE	REF Output Enable	RW	Disabled ¹	Enabled	1
Bit 3		Reserved	•			Х
Bit 2		Reserved				Х
Bit 1	Reserved					X
Bit 0		Reserved				

1. The disabled state depends on Byte11[1:0]. '00' = Low, '01'=HiZ, '10'=Low, '11'=Hlgh

Byte 4 is Reserved

SMBus Table: Revision and Vendor ID Register Byte 5 Name Control Control Function Type 0

Byte 5	Name	Control Function	Туре	0	1	Default
Bit 7	RID3		R	B rev = 0001		0
Bit 6	RID2	Revision ID	R			0
Bit 5	RID1		R			0
Bit 4	RID0		R		1	
Bit 3	VID3		R			0
Bit 2	VID2	VENDOR ID	R	0001		0
Bit 1	VID1		R	- 0001 = IDT		0
Bit 0	VID0		R			1

SMBus Table: Device Type/Device ID

Byte 6	Name	Control Function	Туре	0	1	Default
Bit 7	Device Type1	Device Type	R	00 = FGx,	01 = DBx,	0
Bit 6	Device Type0	Device Type	R	10 = DMx, 11:	0	
Bit 5	Device ID5		R			0
Bit 4	Device ID4	-	R			0
Bit 3	Device ID3	Device ID	R	000110 bina	000110 binary or 06 hex	
Bit 2	Device ID2	Device iD	R		IY OF OUTIER	1
Bit 1	Device ID1		R	1		1
Bit 0	Device ID0]	R			0

SMBus Table: Byte Count Register

Byte 7	Name	Control Function	Туре	0	1	Default
Bit 7	Reserved					
Bit 6	Reserved					
Bit 5	Reserved					
Bit 4	BC4		RW			0
Bit 3	BC3		RW	Writing to this regist	er will configure how	1
Bit 2	BC2	Byte Count Programming	RW	many bytes will be r	ead back, default is	0
Bit 1	BC1		RW	= 8 b	ytes.	0
Bit 0	BC0		RW			0

Bytes 8 and 9 are Reserved.

SMBus Table: PLL MN Enable, PD_Restore

Byte 10	Name	Control Function	Туре	0	1	Default
Bit 7	PLL M/N En ¹	M/N Programming Enable	RW	M/N Prog. Disabled	M/N Prog. Enabled	0
Bit 6	Power-Down (PD) Restore	Restore Default Config. In PD	RW	Clear Config in PD	Keep Config in PD	1
Bit 5	Reserved					
Bit 4		Reserved				Х
Bit 3		Reserved				Х
Bit 2		Reserved				Х
Bit 1	Reserved					Х
Bit 0		Reserved				X

1. This bit is a '1' on 9FGL0xP1 devices

SMBus Table: Stop State Control

Byte 11	Name	Control Function	Туре	0	1	Default	
Bit 7		Reserved				Х	
Bit 6		Reserved				Х	
Bit 5		Reserved				Х	
Bit 4		Reserved				Х	
Bit 3		Reserved				Х	
Bit 2		Reserved				Х	
Bit 1	STP[1]	STP[1] True/Complement DIF Output RW 00 = Low/Low 10 = High/Low					
Bit 0	STP[0]	Disable State	RW	01 = HiZ/HiZ	11 = Low/High	0	

SMBus Table: Impedance Control

Byte 12	Name	Control Function	Туре	0	1	Default
Bit 7	DIF2_imp[1]	DIF2 Zout	RW	00=33Ω DIF Zout	10=100Ω DIF Zout	
Bit 6	DIF2_imp[0]	DIF2 Zout	RW	01=85Ω DIF Zout	11 = Reserved	see Note
Bit 5	DIF1_imp[1]	DIF1 Zout	RW	00=33Ω DIF Zout	10=100Ω DIF Zout	SEE NULE
Bit 4	DIF1_imp[0]	DIF1 Zout	RW	01=85Ω DIF Zout	11 = Reserved	
Bit 3		Reserved				Х
Bit 2		Reserved				Х
Bit 1	DIF0_imp[1]	DIF0 Zout	RW	00=33Ω DIF Zout	10=100Ω DIF Zout	see Note
Bit 0	DIF0_imp[0]	DIF0 Zout	RW	01=85Ω DIF Zout	11 = Reserved	See Note

SMBus Table: Impedance Control

Byte 13	Name	Control Function	Туре	0	1	Default
Bit 7	DIF5_imp[1]	DIF5 Zout	RW	00=33Ω DIF Zout	10=100Ω DIF Zout	
Bit 6	DIF5_imp[0]	DIF5 Zout	RW	01=85Ω DIF Zout	11 = Reserved	see Note
Bit 5	DIF4_imp[1]	DIF4 Zout	RW	00=33Ω DIF Zout	10=100Ω DIF Zout	SEE NULE
Bit 4	DIF4_imp[0]	DIF6 Zout	RW	01=85Ω DIF Zout	11 = Reserved	
Bit 3		Reserved	•			Х
Bit 2		Reserved				Х
Bit 1	DIF3_imp[1]	DIF3 Zout	RW	00=33Ω DIF Zout	10=100Ω DIF Zout	see Note
Bit 0	DIF3_imp[0]	DIF3 Zout	RW	01=85Ω DIF Zout	11 = Reserved	See Note

SMBus Table: Pull-up Pull-down Control

Byte 14	Name	Control Function	Туре	0	1	Default
Bit 7	OE2_pu/pd[1]	OE2_pu/pd[1] OE2 Pull-up(PuP)/		00=None	10=Pup	0
Bit 6	OE2_pu/pd[0]	Pull-down(Pdwn) control	RW	01=Pdwn	11 = Pup+Pdwn	1
Bit 5	OE1_pu/pd[1]	OE1 Pull-up(PuP)/	RW	00=None	10=Pup	0
Bit 4	OE1_pu/pd[0]	Pull-down(Pdwn) control	RW	01=Pdwn	11 = Pup+Pdwn	1
Bit 3		Reserved				Х
Bit 2		Reserved				Х
Bit 1	OE0_pu/pd[1]	OE0 Pull-up(PuP)/	RW	00=None	10=Pup	0
Bit 0	OE0_pu/pd[0]	Pull-down(Pdwn) control	RW	01=Pdwn	11 = Pup+Pdwn	1

SMBus Table: Pull-up Pull-down Control

Byte 15	Name	Control Function	Туре	0	1	Default
Bit 7	OE5_pu/pd[1]	OE5 Pull-up(PuP)/	RW	00=None	10=Pup	0
Bit 6	OE5_pu/pd[0]	Pull-down(Pdwn) control	RW	01=Pdwn	11 = Pup+Pdwn	1
Bit 5	OE4_pu/pd[1]	OE4 Pull-up(PuP)/	RW	00=None	10=Pup	0
Bit 4	OE4_pu/pd[0]	Pull-down(Pdwn) control	RW	01=Pdwn	11 = Pup+Pdwn	1
Bit 3		Reserved				Х
Bit 2		Reserved				Х
Bit 1	OE3_pu/pd[1]	OE3 Pull-up(PuP)/	RW	00=None	10=Pup	0
Bit 0	OE3_pu/pd[0]	Pull-down(Pdwn) control	RW	01=Pdwn	11 = Pup+Pdwn	1

SMBus Table: Pull-up Pull-down Control

Byte 16	Name	Control Function	Туре	0	1	Default
Bit 7		Reserved				Х
Bit 6		Reserved				Х
Bit 5		Reserved				Х
Bit 4		Reserved				Х
Bit 3		Reserved				Х
Bit 2		Reserved				Х
Bit 1	CKPWRGD_PD_pu/pd[1] CKPWRGD_PD Pull-up(PuP)/ RW 00=None 10=Pup					
Bit 0	CKPWRGD_PD_pu/pd[0]					0

Bytes 17 is Reserved

SMBus Table: Polarity Control

Byte 18	Name	Control Function	Туре	0	1	Default
Bit 7	OE5_polarity	Sets OE5 polarity	RW	Enabled when Low	Enabled when High	0
Bit 6	OE4_polarity	Sets OE4 polarity	RW	Enabled when Low	Enabled when High	0
Bit 5		Reserved				Х
Bit 4	OE3_polarity	Sets OE3 polarity	RW	Enabled when Low	Enabled when High	0
Bit 3	OE2_polarity	Sets OE2 polarity	RW	Enabled when Low	Enabled when High	0
Bit 2	OE1_polarity	Sets OE1 polarity	RW	Enabled when Low	Enabled when High	0
Bit 1		Reserved				Х
Bit 0	OE0_polarity	Sets OE0 polarity	RW	Enabled when Low	Enabled when High	0

SMBus Table: Polarity Control

Byte 19	Name	Control Function	Туре	0	1	Default	
Bit 7		Reserved					
Bit 6		Reserved					
Bit 5		Reserved				Х	
Bit 4		Reserved				Х	
Bit 3		Reserved				Х	
Bit 2		Reserved				Х	
Bit 1		Reserved				Х	
Bit 0	CKPWRGD_PD	Determines CKPWRGD_PD polarity	RW	Power Down when Low	Power Down when High	0	

Recommended Crystal Characteristics (3225 package)

PARAMETER	VALUE	UNITS	NOTES
Frequency	25	MHz	1
Resonance Mode	Fundamental	-	1
Frequency Tolerance @ 25°C	±20	PPM Max	1
Frequency Stability, ref @ 25°C Over	+20	PPM Max	1
Operating Temperature Range			
Temperature Range (commerical)	0~70	°C	1
Temperature Range (industrial)	-40~85	°C	1
Equivalent Series Resistance (ESR)	50	Ω Max	1
Shunt Capacitance (C _O)	7	pF Max	1
Load Capacitance (C _L)	8	pF Max	1
Drive Level	0.3	mW Max	1
Aging per year	±5	PPM Max	1

Notes:

1. FOX 603-25-150JA4C

Marking Diagrams



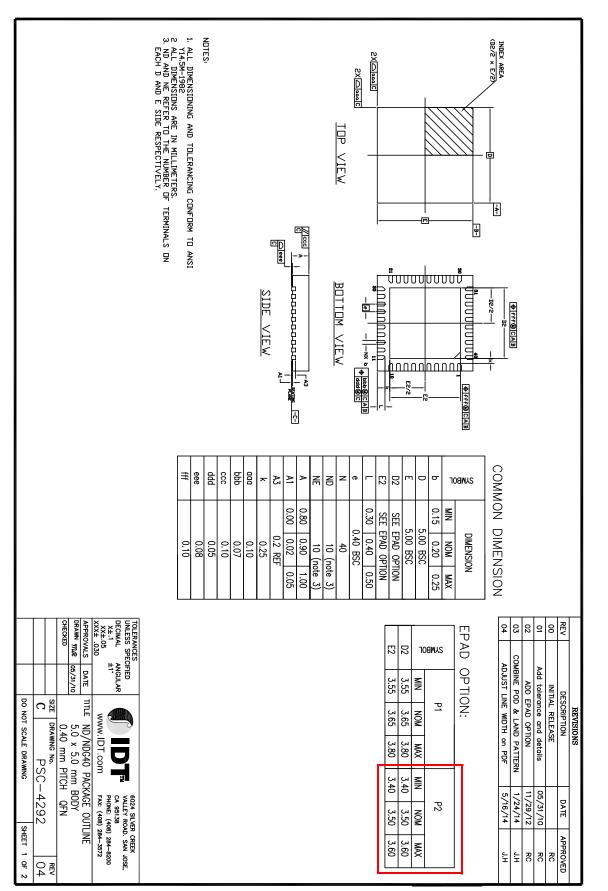
Notes:

- 1. "LOT" is the lot sequence number.
- 2. "COO" denotes country of origin.
- 3. "YYWW" is the last two digits of the year and week that the part was assembled.
- 4. Line 2: truncated part number
- 5. "L" denotes RoHS compliant package.
- 6. "I" denotes industrial temperature range device.
- 7. "P" denotes factory programmable defaults

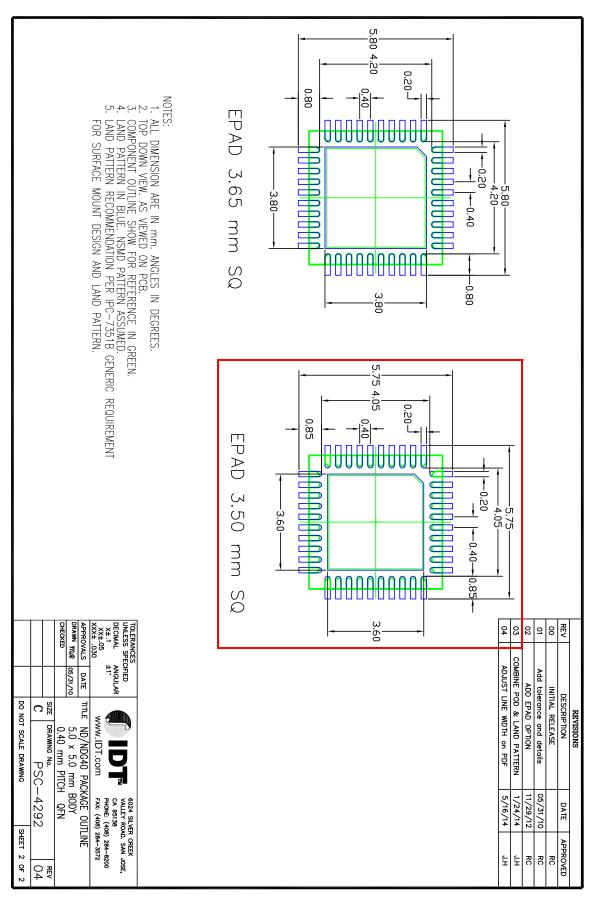
Thermal Characteristics

PARAMETER	SYMBOL	CONDITIONS	PKG	TYP.	UNITS	NOTES
	$\theta_{\rm JC}$	Junction to Case		42	°C/W	1
	θ_{Jb}	Junction to Base		2.4	°C/W	1
Thermal Resistance	θ_{JA0}	Junction to Air, still air	NDG40	39	°C/W	1
memai nesistance	θ_{JA1}	Junction to Air, 1 m/s air flow	NDG40	33	°C/W	1
	θ_{JA3}	Junction to Air, 3 m/s air flow		28	°C/W	1
	θ_{JA5}	Junction to Air, 5 m/s air flow		27	°C/W	1

¹ePad soldered to board



Package Outline and Package Dimensions (NDG40) – use EPAD 3.50 mm SQ



Ordering Information

Part / Order Number	Notes	Shipping Packaging	Package	Temperature
9FGL0641BKILF	100Ω	Trays	40-pin VFQFPN	-40 to +85° C
9FGL0641BKILFT	10022	Tape and Reel	40-pin VFQFPN	-40 to +85° C
9FGL0651BKILF	85Ω	Trays	40-pin VFQFPN	-40 to +85° C
9FGL0651BKILFT	0012	Tape and Reel	40-pin VFQFPN	-40 to +85° C
9FGL06P1BxxxKILF	Factory configurable. Contact IDT for	Trays	40-pin VFQFPN	-40 to +85° C
9FGL06P1BxxxKILFT	addtional information.	Tape and Reel	40-pin VFQFPN	-40 to +85° C

"LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

"B" is the device revision designator (will not correlate with the datasheet revision).

"xxx" is a unique factory assigned number to identify a particular default configuration.

Revision History

Rev.	Issue Date	Intiator	Description	Page #
E	6/3/2016	RDW	 Update electrical tables for B rev production release Added PCIe SRIS and PCIe Gen4 CC to phase jitter tables. Updated front page text. Removed '000' blank device from ordering information. Updated Byte0 wording for clarity Updated Byte1[1:0] descriptions. 	Various
F	6/22/12016	RDW	 Updated electrical tabels with final data from PE/TE Minor cleanup of the SMBus descriptions. Release 	Various
G	9/2/12016	RDW	1. Corrected Byte 2 to properly indicate slew rate control bits	11
Н	10/19/2016	RDW	Removed IDT crystal part number	



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